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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HAT2116H

Silicon N Channel Power MOS FET
Power Switching

RENESAS

ADE-208-1575B (Z)

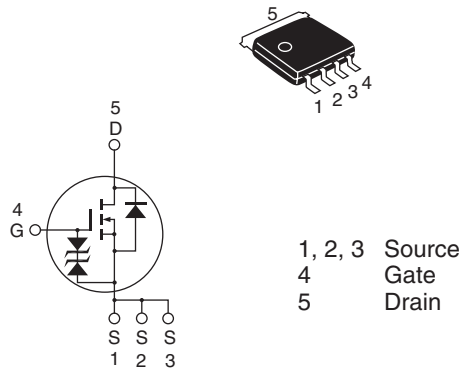
3rd. Edition
Aug. 2002

Features

- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
 $R_{DS(on)} = 6.3 \text{ m}\Omega$ typ. (at $V_{GS} = 10 \text{ V}$)

Outline

LFPAK



Absolute Maximum Ratings

(Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|--|---------------------------------|---------------|------|
| Drain to source voltage | V_{DSS} | 30 | V |
| Gate to source voltage | V_{GSS} | ± 20 | V |
| Drain current | I_D | 30 | A |
| Drain peak current | $I_{D(pulse)}$ ^{Note1} | 120 | A |
| Body-drain diode reverse drain current | I_{DR} | 30 | A |
| Channel dissipation | Pch ^{Note2} | 15 | W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | – 55 to + 150 | °C |

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

2. $T_c = 25^\circ C$

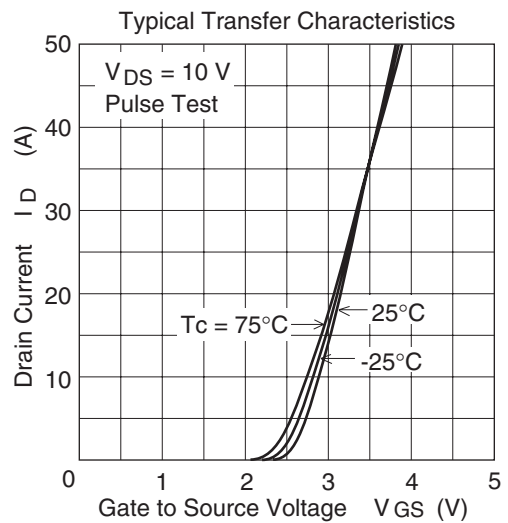
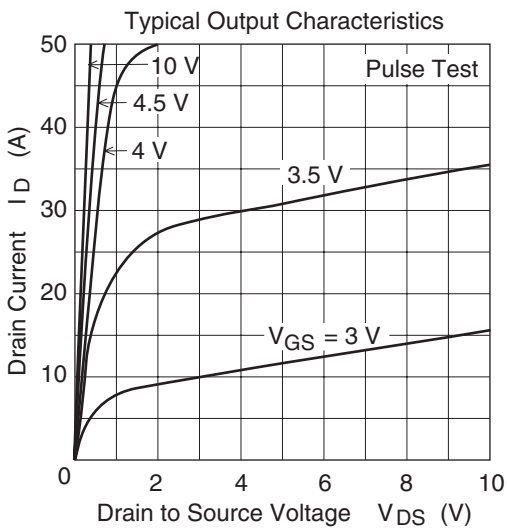
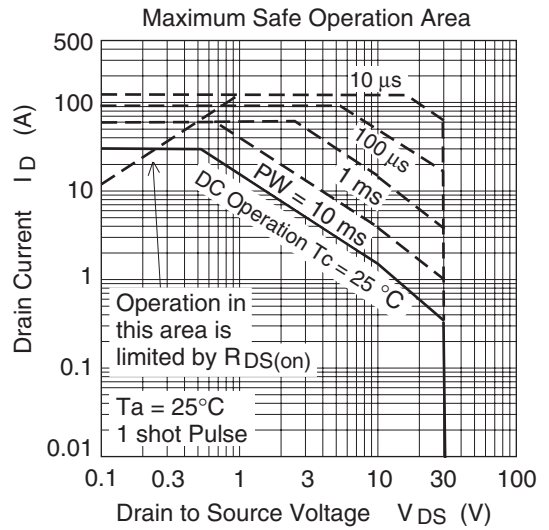
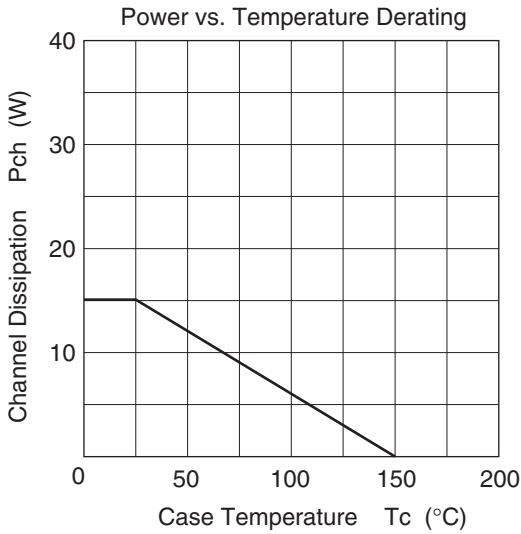
Electrical Characteristics

(Ta = 25°C)

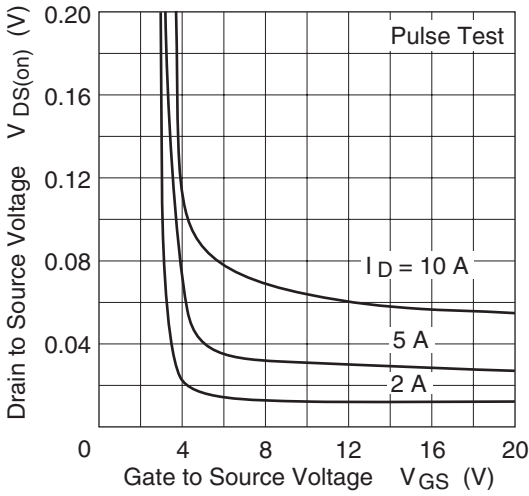
| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|--|---------------|----------|------|----------|------------------|--|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 30 | — | — | V | $I_D = 10 \text{ mA}$, $V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ± 20 | — | — | V | $I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$ |
| Gate to source leak current | I_{GSS} | — | — | ± 10 | μA | $V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$ |
| Zero gate voltage drain current | I_{DSS} | — | — | 1 | μA | $V_{DS} = 30 \text{ V}$, $V_{GS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 1.0 | — | 2.5 | V | $V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$ |
| Static drain to source on state resistance | $R_{DS(on)}$ | — | 6.3 | 8.2 | $\text{m}\Omega$ | $I_D = 15 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note3} |
| | $R_{DS(on)}$ | — | 10.5 | 15.3 | $\text{m}\Omega$ | $I_D = 15 \text{ A}$, $V_{GS} = 4.5 \text{ V}$ ^{Note3} |
| Forward transfer admittance | $ y_{fs} $ | 27 | 45 | — | S | $I_D = 15 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note3} |
| Input capacitance | Ciss | — | 1650 | — | pF | $V_{DS} = 10 \text{ V}$ |
| Output capacitance | Coss | — | 400 | — | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | Crss | — | 220 | — | pF | $f = 1 \text{ MHz}$ |
| Total gate charge | Qg | — | 26 | — | nc | $V_{DD} = 10 \text{ V}$ |
| Gate to source charge | Qgs | — | 5 | — | nc | $V_{GS} = 10 \text{ V}$ |
| Gate to drain charge | Qgd | — | 5 | — | nc | $I_D = 30 \text{ A}$ |
| Turn-on delay time | $t_{d(on)}$ | — | 15 | — | ns | $V_{GS} = 10 \text{ V}$, $I_D = 15 \text{ A}$ |
| Rise time | t_r | — | 55 | — | ns | $V_{DD} \cong 10 \text{ V}$ |
| Turn-off delay time | $t_{d(off)}$ | — | 48 | — | ns | $R_L = 0.5 \text{ }\Omega$ |
| Fall time | t_f | — | 11 | — | ns | $R_g = 4.7 \text{ }\Omega$ |
| Body-drain diode forward voltage | V_{DF} | — | 0.85 | 1.11 | V | $I_F = 30 \text{ A}$, $V_{GS} = 0$ ^{Note3} |
| Body-drain diode reverse recovery time | t_{rr} | — | 60 | — | ns | $I_F = 30 \text{ A}$, $V_{GS} = 0$ $diF/dt = 50 \text{ A}/\mu\text{s}$ |

Notes: 3. Pulse test

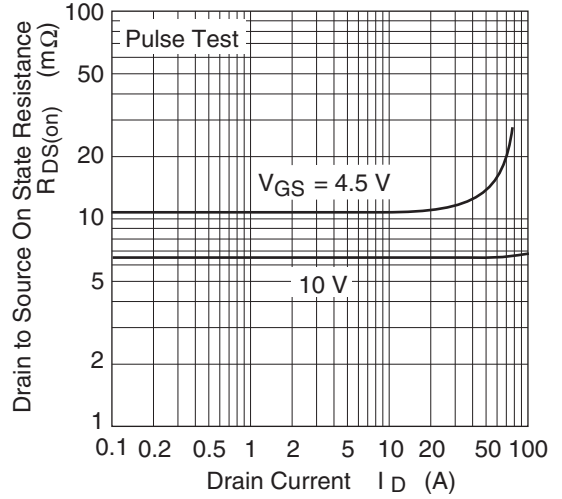
Main Characteristics



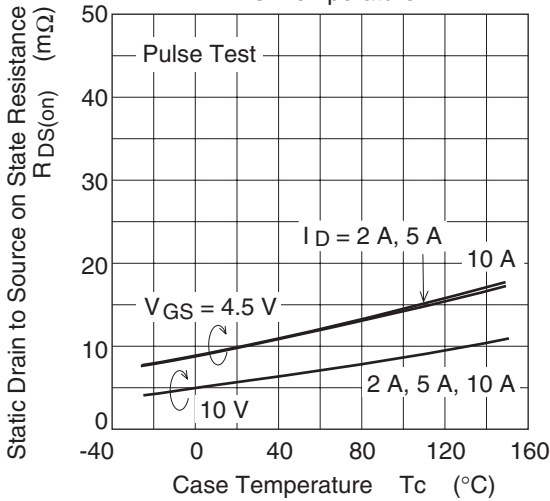
Drain to Source Saturation Voltage vs. Gate to Source Voltage



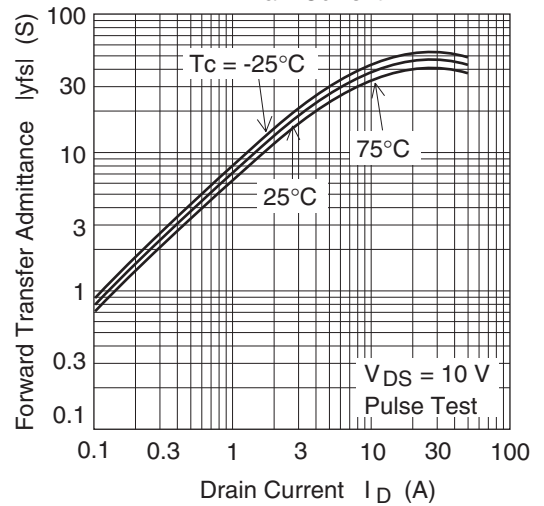
Static Drain to Source on State Resistance vs. Drain Current



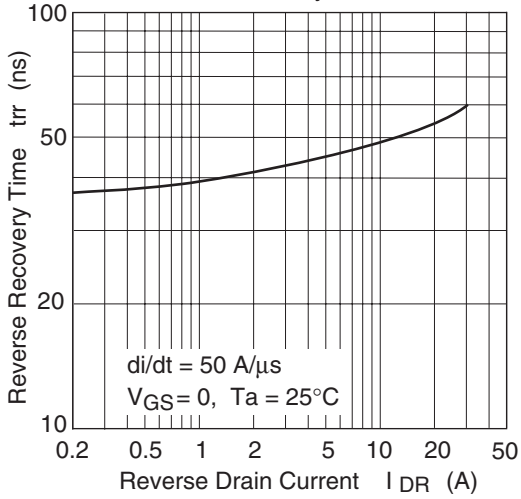
Static Drain to Source on State Resistance vs. Temperature



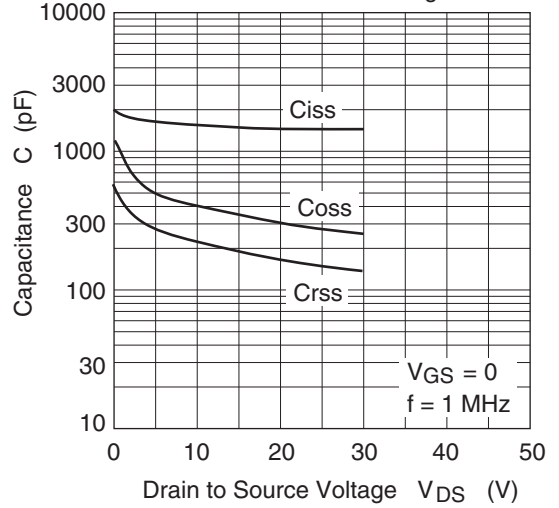
Forward Transfer Admittance vs. Drain Current



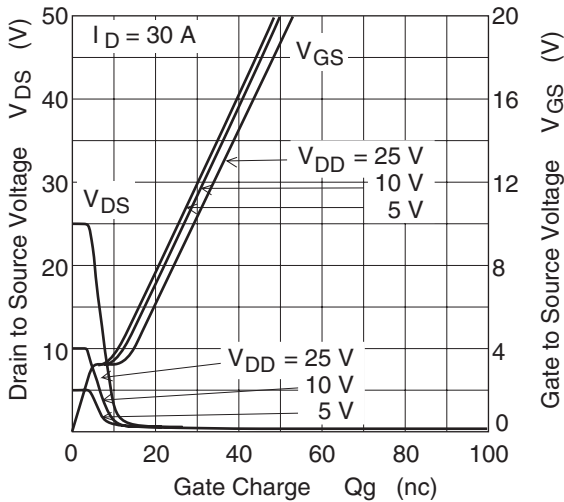
Body-Drain Diode Reverse Recovery Time



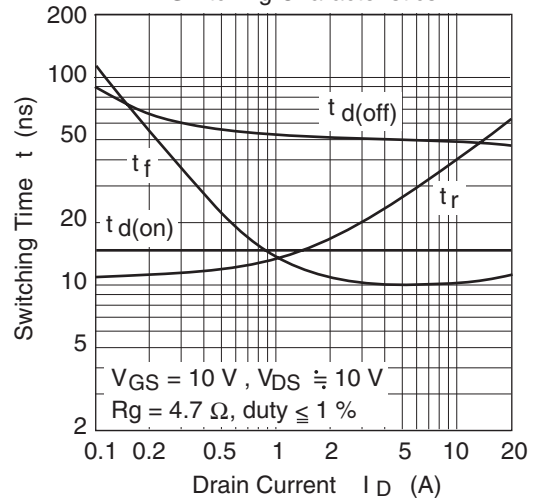
Typical Capacitance vs. Drain to Source Voltage

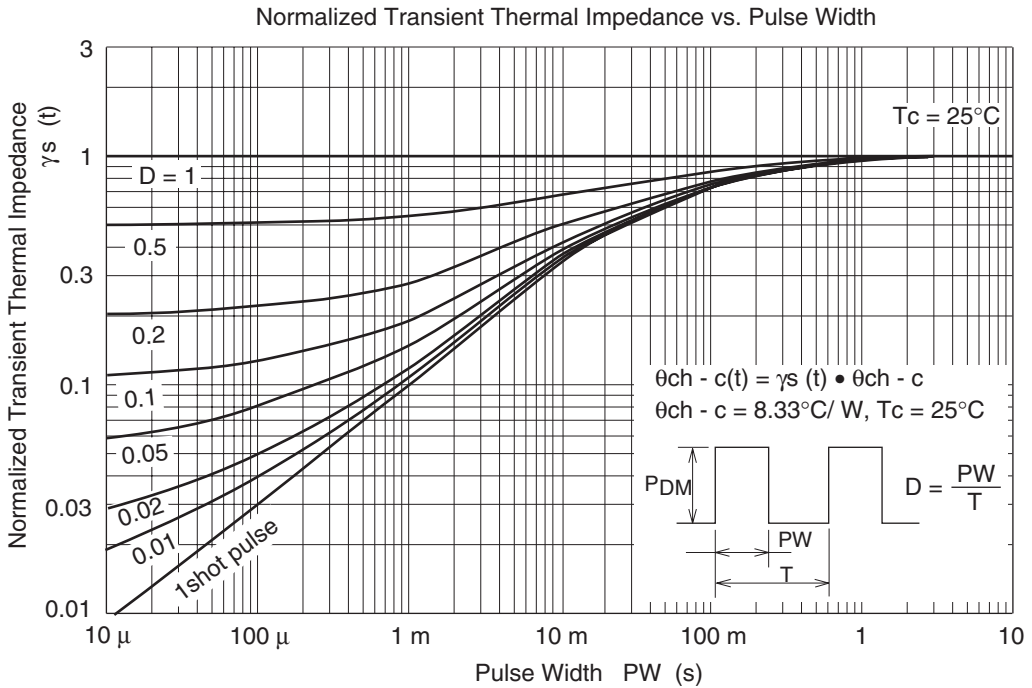
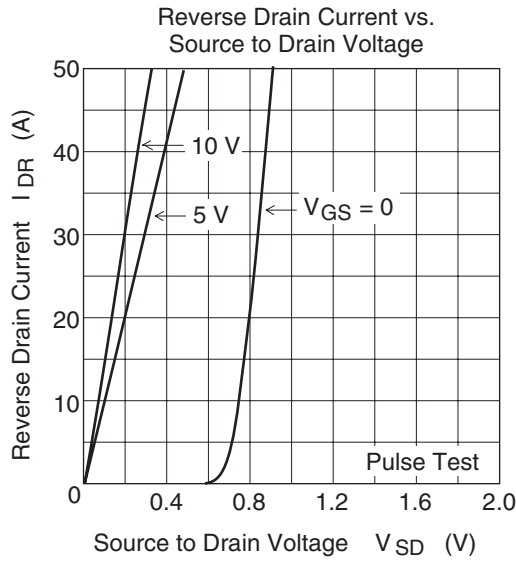


Dynamic Input Characteristics

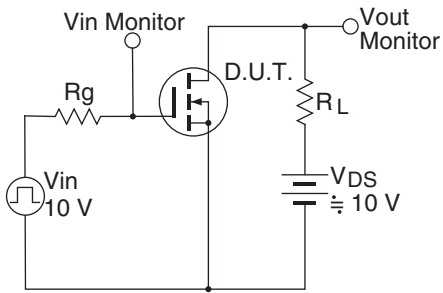


Switching Characteristics

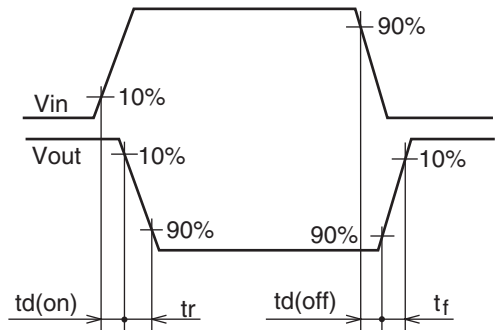




Switching Time Test Circuit



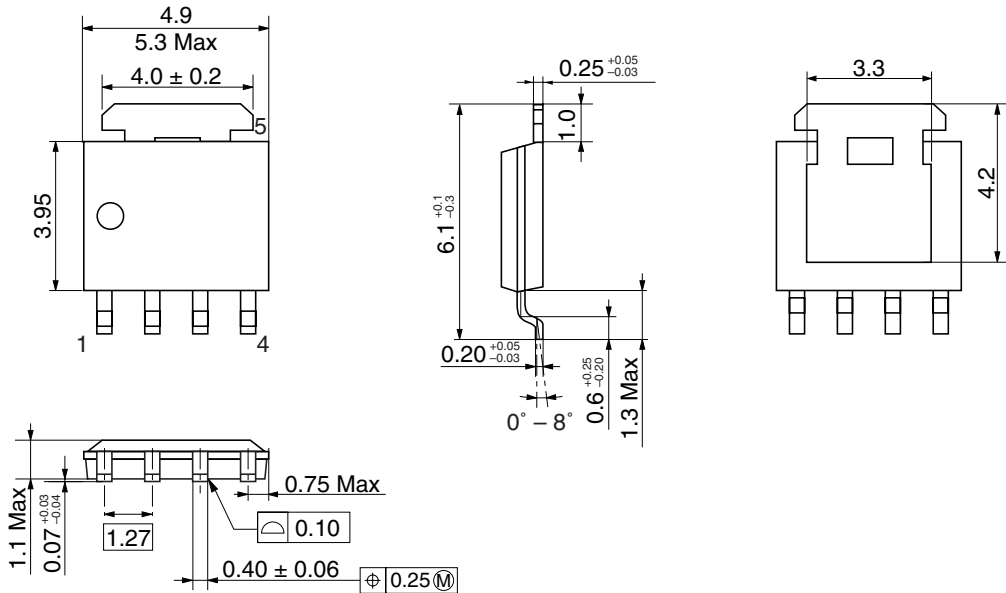
Switching Time Waveform



Package Dimensions

As of January, 2002

Unit: mm



| | |
|------------------------|---------|
| Hitachi Code | LFPAK |
| JEDEC | — |
| JEITA | — |
| Mass (reference value) | 0.080 g |

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Colophon 6.0



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